AMENDMENT

(Amendment based upon the provision of Article 11 of said Law)

To: Examiner of the Patent Office

1. Identification of the International Application
PCT/JP2004/004072

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4. Item to be amended: Claims

5. Subject Matter of Amendment

The applicant has amended claim 1, and claims 2 to 4 are unchanged. The whole wording of claim 1 has been rewritten in order to make the feature of claim 1 clear. Support for change to "a non-doped layer stacked on the silicon substrate, the non-doped layer having an amorphous silicon phase and a microcrystalline silicon phase mixed together" can be found at page 9, line 25 to page 10, line 1 of the specification.

6. List of Attached Documents

(1) Replacement sheet of page 49

CLAIMS

1. (Amended) A solar cell comprising:

a silicon substrate for a solar cell, the substrate comprising a base composed of a polycrystalline metal-grade silicon solidified in one direction and a high-purity polycrystalline silicon layer stacked on a surface of the base; and

a non-doped layer stacked on the silicon substrate, the non-doped layer having an amorphous silicon phase and a microcrystalline silicon phase mixed together.

2. (Unchanged) A solar cell according to claim 1, wherein a thickness of the layer having the non-doped amorphous silicon phase and the microcrystalline silicon phase mixed together ranges from 1 nm to 15 nm.

3. (Unchanged) A solar cell according to claim 1 or 2, wherein a ratio of the amorphous silicon phase and the microcrystalline silicon phase in the layer having the non-doped amorphous silicon phase and the microcrystalline silicon phase mixed together ranges from 1:1 to 10:1.

4. (Unchanged) A solar cell comprising a crystalline silicon substrate or a crystalline silicon layer, a layer having an amorphous silicon phase and a microcrystalline silicon phase mixed together, and a polycrystalline silicon layer grown with the microcrystalline silicon phase as a seed, which are stacked in mentioned order.